

ABSTRACT OF THE DISCLOSURE

The present invention is a method for producing a single crystal by Czochralski method with pulling a seed crystal from a raw material melt, wherein when a pulling rate of pulling a single crystal is defined as V (mm/min), a temperature gradient at a solid-liquid interface is defined as G (K/mm) and a highest temperature at an interface between a crucible and a raw material melt is defined as T_{\max} ($^{\circ}\text{C}$), at least, a range of a value of V/G ($\text{mm}^2/\text{K}\cdot\text{min}$) including a desired defect region and/or a desired defect-free region is determined according to the T_{\max} ($^{\circ}\text{C}$), and the single crystal is pulled with controlling a value of V/G ($\text{mm}^2/\text{K}\cdot\text{min}$) within the determined range. There can be provided a method for producing a single crystal in which when a single crystal is pulled with controlling a value of V/G , a value of V/G including a desired defect region and/or a desired defect-free region can be determined more precisely and a single crystal with desired quality can be more surely pulled.